

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	40	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Notes 6, 9)	I _D	100 100	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	200	A
Continuous Body Diode Forward Current (Note 6)	I _S	85	A
Avalanche Current, L = 0.1mH	I _{AS}	48	A
Avalanche Energy, L = 0.1mH	E _{AS}	115	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	2.3	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	55	°C/W
Total Power Dissipation (Note 6)	P _D	104	W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	1.2	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	40	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 32V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.3	1.8	mΩ	V _{GS} = 10V, I _D = 25A
		—	2	3.1		V _{GS} = 4.5V, I _D = 25A
Diode Forward Voltage	V _{SD}	—	—	1.2	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	6771	—	pF	V _{DS} = 20V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{OSS}	—	2165	—		
Reverse Transfer Capacitance	C _{rss}	—	176	—		
Gate Resistance	R _G	—	0.85	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	116.1	—	nC	V _{DD} = 20V, I _D = 25A, V _{GS} = 10V
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	55.2	—		
Gate-Source Charge	Q _{gs}	—	20.3	—		
Gate-Drain Charge	Q _{gd}	—	22.7	—	ns	V _{DD} = 20V, V _{GS} = 10V, I _D = 25A, R _G = 3Ω
Turn-On Delay Time	t _{D(ON)}	—	11.4	—		
Turn-On Rise Time	t _R	—	22.9	—		
Turn-Off Delay Time	t _{D(OFF)}	—	62.5	—		
Turn-Off Fall Time	t _F	—	28	—	ns	I _F = 25A, di/dt = 100A/µs
Reverse Recovery Time	t _{RR}	—	58.6	—		
Reverse Recovery Charge	Q _{RR}	—	107	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.
 - Package limited.

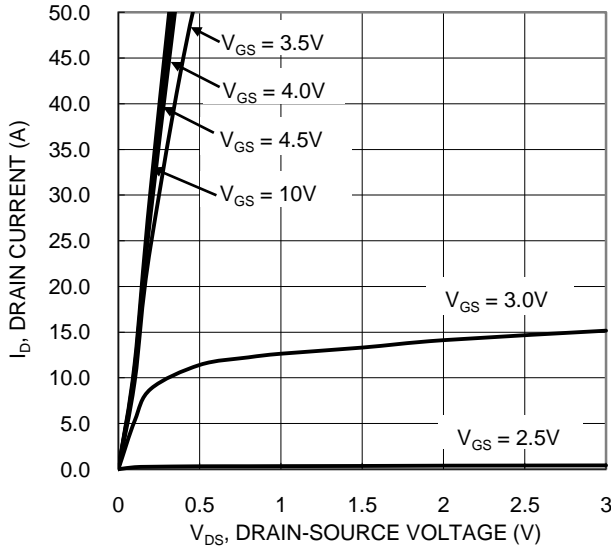


Figure 1. Typical Output Characteristic

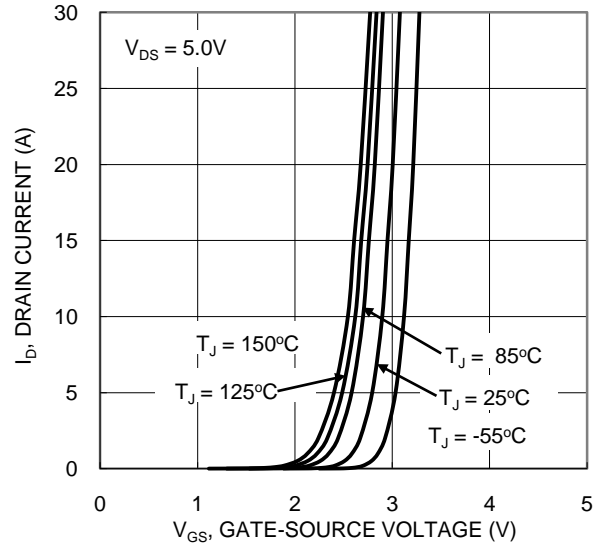


Figure 2. Typical Transfer Characteristic

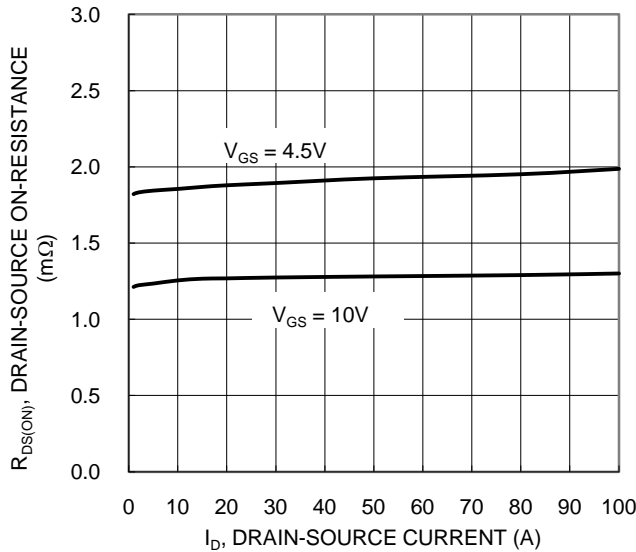


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

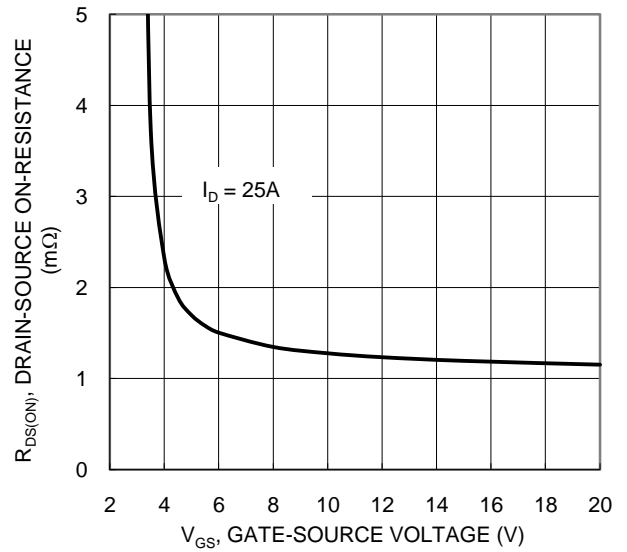


Figure 4. Typical Transfer Characteristic

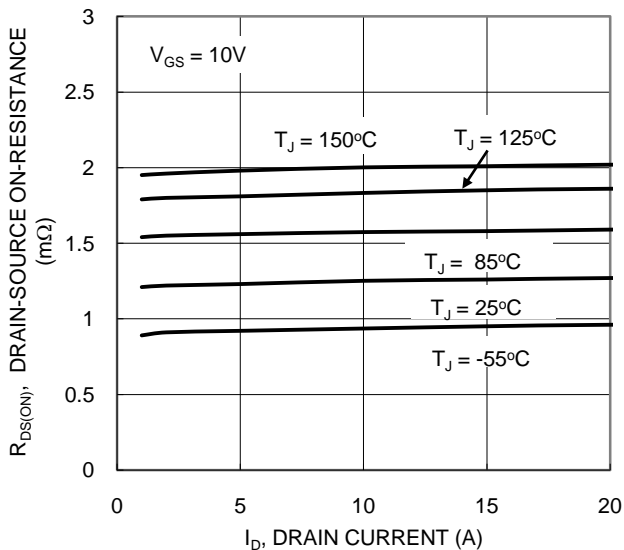


Figure 5. Typical On-Resistance vs Drain Current and Temperature

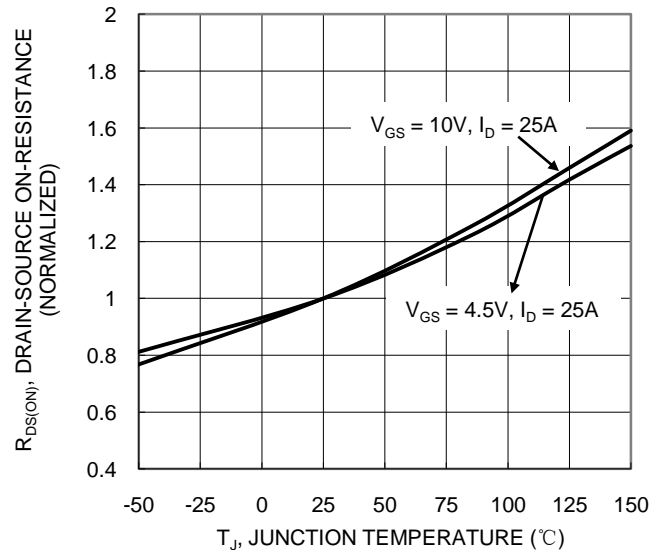


Figure 6. On-Resistance Variation with Temperature

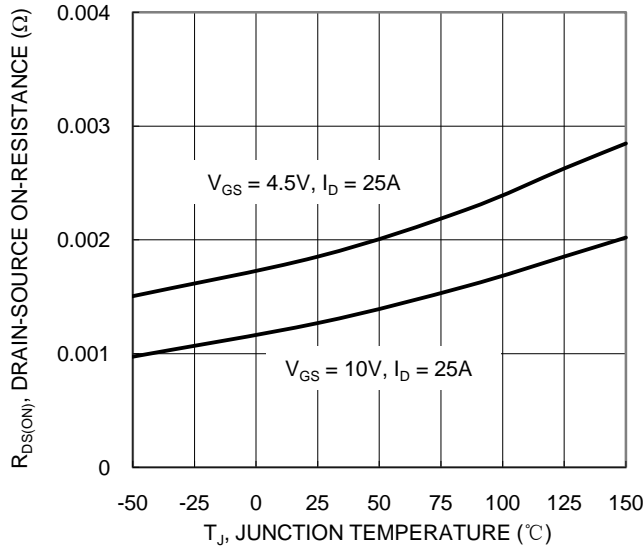


Figure 7. On-Resistance Variation with Temperature

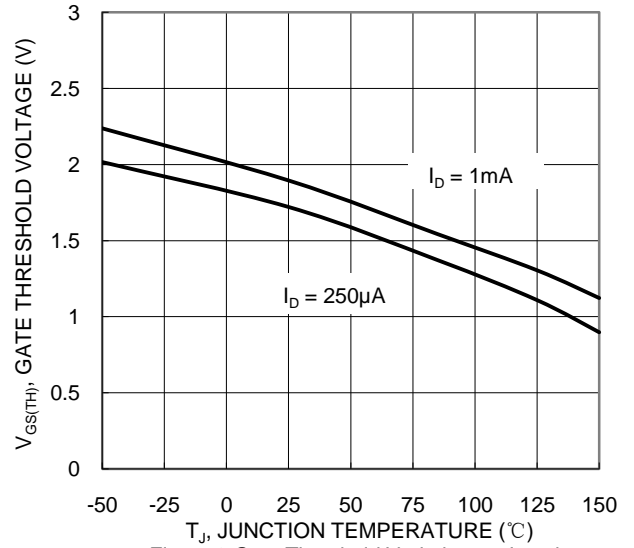


Figure 8 Gate Threshold Variation vs Junction Temperature

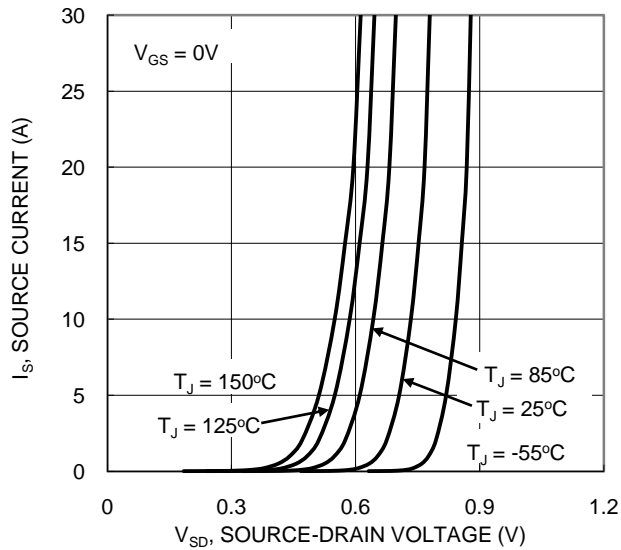


Figure 9. Diode Forward Voltage vs Current

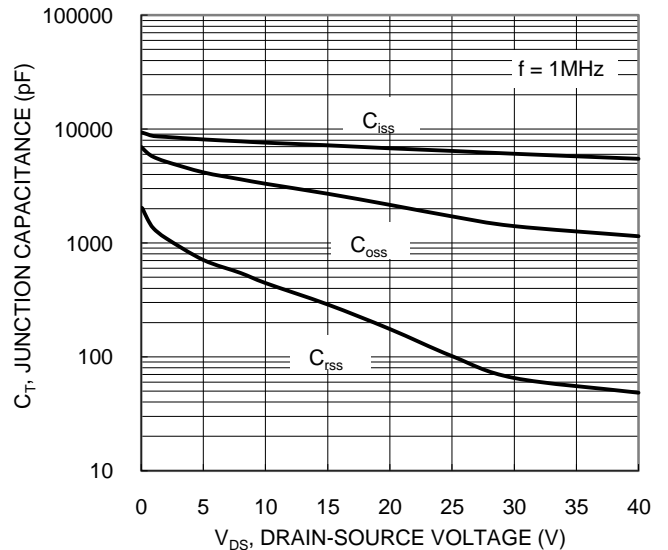


Figure 10. Typical Junction Capacitance

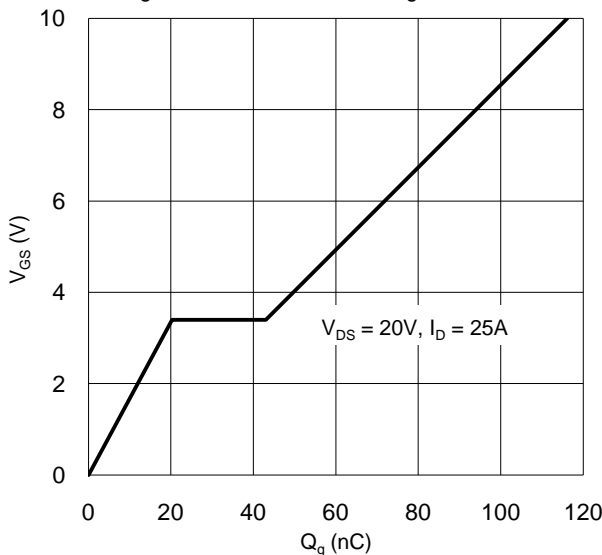


Figure 11. Gate Charge

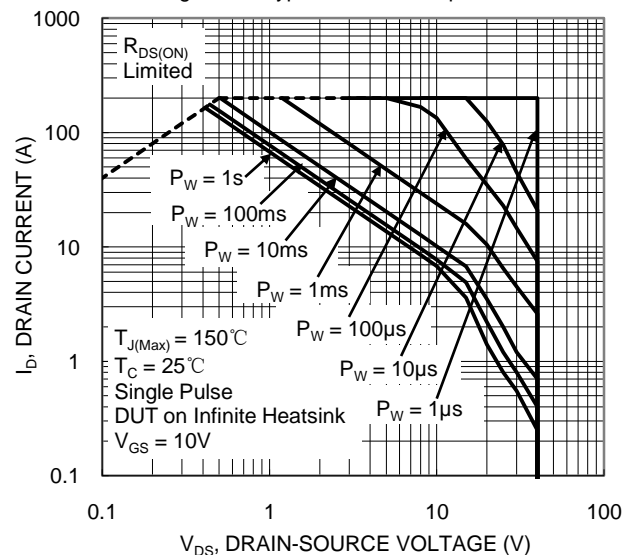


Figure 12. SOA, Safe Operation Area

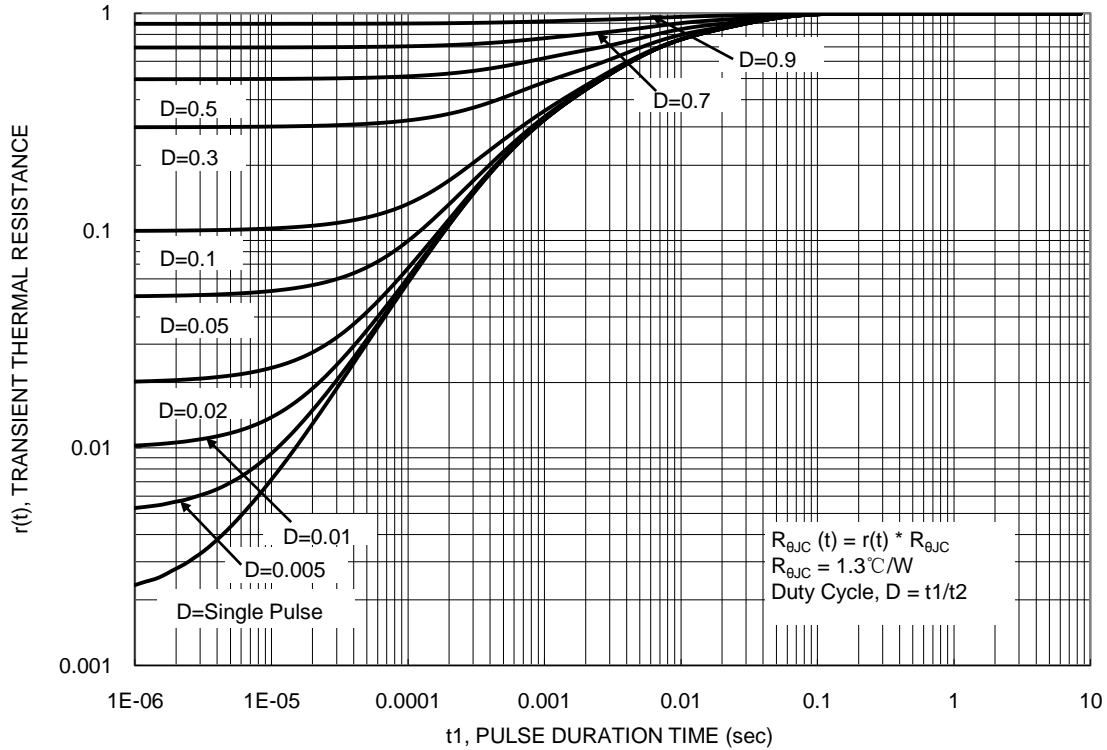
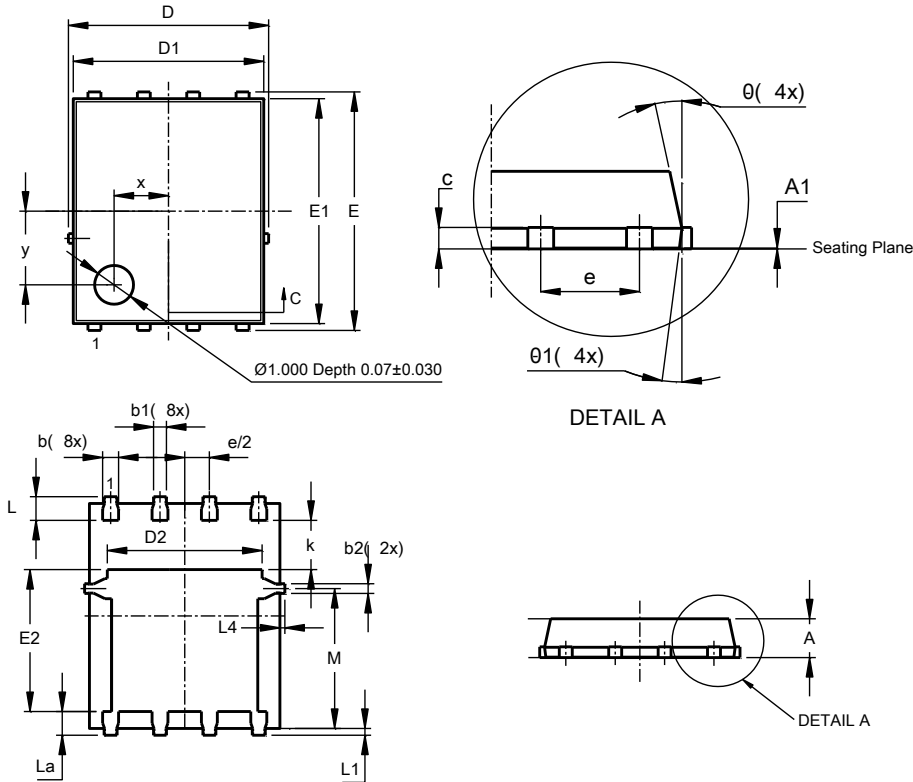


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type K)

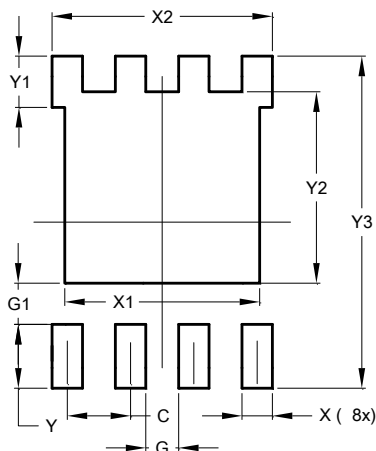


PowerDI5060-8 (Type K)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	0.02
b	0.33	0.51	0.41
b1	0.300	0.366	0.333
b2	0.20	0.35	0.25
c	0.23	0.33	0.277
D	5.15 BSC		
D1	4.85	4.95	4.90
D2	-	-	3.98
E	6.15 BSC		
E1	5.75	5.85	5.80
E2	3.56	3.725	3.66
E	1.27BSC		
k	-	-	1.27
L	0.51	0.71	0.61
La	0.51	0.675	0.61
L1	0.05	0.20	0.175
L4	-	-	0.125
M	3.50	3.71	3.605
x	-	-	1.400
y	-	-	1.900
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type K)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	3.910
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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